

# **SS9014**

# Pre-Amplifier, Low Level & Low Noise

- High total power dissipation. (P<sub>T</sub>=450mW)
- High h<sub>FE</sub> and good linearity
- Complementary to SS9015



### 1. Emitter 2. Base 3. Collector

# **NPN Epitaxial Silicon Transistor**

# **Absolute Maximum Ratings** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{CBO}$	Collector-Base Voltage	50	V
V <sub>CEO</sub>	Collector-Emitter Voltage	45	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current	100	mA
P <sub>C</sub>	Collector Power Dissipation	450	mW
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

# Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	50			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_C = 1 \text{ mA}, I_B = 0$	45			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	5			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = 50V, I_{E} = 0$			50	nA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 5V$ , $I_C = 0$			50	nA
h <sub>FE</sub>	DC Current Gain	$V_{CE}$ =5V, $I_{C}$ =1mA	60	280	1000	
V <sub>CE</sub> (sat)	Collector-Base Saturation Voltage	I <sub>C</sub> =100mA, I <sub>B</sub> =5mA		0.14	0.3	
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> =100mA, I <sub>B</sub> =5mA		0.84	1.0	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	$V_{CE}$ =5V, $I_{C}$ =2mA	0.58	0.63	0.7	V
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =10V, I <sub>E</sub> =0 f=1MHz		2.2	3.5	pF
f <sub>T</sub>	Current Gain Bandwidth Product	$V_{CE} = 5V$ , $I_{C} = 10mA$	150	270		MHz
NF	Noise Figure	$V_{CE}$ =5V, $I_{C}$ =0.2mA f=1KHz, $R_{S}$ =2K $\Omega$		0.9	10	dB

# **h**<sub>FE</sub> Classification

Classification	Α	В	С	D
h <sub>FE</sub>	60 ~ 150	100 ~ 300	200 ~ 600	400 ~ 1000

# **Typical Characteristics**

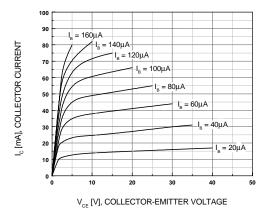


Figure 1. Static Characteristic

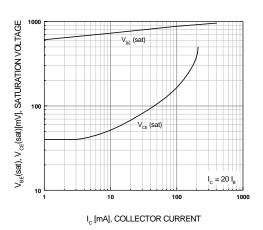


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

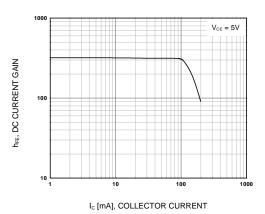


Figure 2. DC current Gain

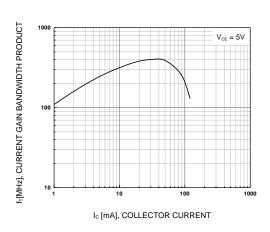
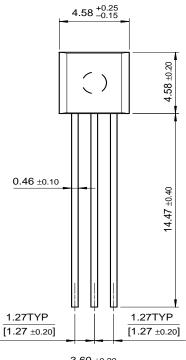
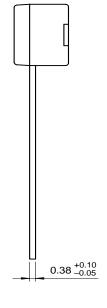


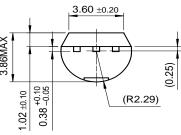
Figure 4. Current Gain Bandwidth Product

# **Package Dimensions**

TO-92







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